ZXM61P02F

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = 25°C
-20V	600mΩ @ V_{GS} = -4.5V	-0.92A
	900mΩ @ V_{GS} = -2.7V	-0.75A

Description and Applications

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

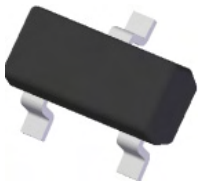
Features and Benefits

- Fast switching speed
- Low on-resistance
- Low threshold
- Low gate drive
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

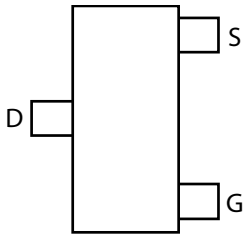
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

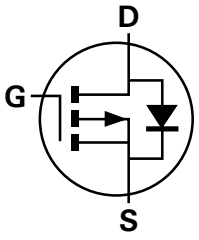
SOT23



Top View



Top View
Pin Out



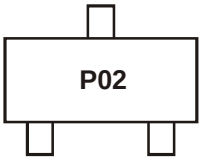
Equivalent Circuit

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXM61P02FTA	P02	7	8	3000 Units

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
2. Diodes Inc's "Green" Policy can be found on our website at http://www.twtysemi.com
3. For packaging details, go to our website at http://www.twtysemi.com

Marking Information



P02 = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GS}	±12	V
Continuous Drain Current	V_{GS} = 4.5V	T_A = 25°C (Note 5) T_A = 70°C (Note 5)	I_D	-0.9 -0.7	A
Pulsed Drain Current (Note 6)			I_{DM}	-4.9	A
Continuous Source Current (Body Diode) (Note 5)			I_S	-0.9	A
Pulsed Source Current (Body Diode) (Note 6)			I_{SM}	-4.9	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) Linear Derating Factor	P_D	625 5	mW mW/°C
Power Dissipation (Note 5) Linear Derating Factor	P_D	806 6.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	155	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
5. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
6. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10μs - pulse current limited by maximum junction temperature.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	I_D = -250μA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-0.1	μA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	-0.7	—	—	V	I_D = -250μA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 7)	$R_{DS\ (ON)}$	—	—	0.6	Ω	V_{GS} = -4.5V, I_D = -0.61A
				0.9		V_{GS} = -2.7V, I_D = -0.31A
Forward Transconductance (Notes 7 and 9)	g_{fs}	0.56	—	—	S	V_{DS} = -10V, I_D = -0.31A
Diode Forward Voltage (Note 7)	V_{SD}	—	—	-0.95	V	T_J = 25°C, I_S = -0.61A, V_{GS} = 0V
Reverse Recovery Time (Note 9)	t_{rr}	—	14.9	—	ns	T_J = 25°C, I_F = -0.61A, di/dt = 100A/μs
Reverse Recovery Charge (Note 9)	Q_{rr}	—	5.6	—	nC	
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	150	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	70	—		
Reverse Transfer Capacitance	C_{rss}	—	30	—		
Turn-On Delay Time (Note 8)	$t_{d(on)}$	—	2.9	—	ns	V_{DD} = -110V, I_D = -0.93A, $R_G \cong 6.2\Omega$, $R_D \cong 11\Omega$,
Turn-On Rise Time (Note 8)	t_r	—	6.7	—		
Turn-Off Delay Time (Note 8)	$t_{d(off)}$	—	11.2	—		
Turn-Off Fall Time (Note 8)	t_f	—	10.1	—		
Total Gate Charge (Note 8)	Q_g	—	3.5	—	nC	V_{DS} = -16V, V_{GS} = -4.5V, I_D = -0.61A
Gate-Source Charge (Note 8)	Q_{gs}	—	0.5	—		
Gate-Drain Charge (Note 8)	Q_{gd}	—	1.5	—		

Notes:
7. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.
8. Switching characteristics are independent of operating junction temperature.
9. For design aid only, not subject to production testing.